

ABSTRACT OF THE DISCLOSURE

In order to provide a reliable surge protective component with
a straightforward manufacturing process, first and second
buried layers are diffused over the entire inside surfaces of
5 a semiconductor substrate, and first and second base layers
are then diffused over the entire inside surfaces of the first
and second buried layers. First and second emitter layers are
then partially diffused at the inside of the first and second
base layers. The peripheries of the first and second emitter
10 layers are then surrounded by first and second moats, the
bottoms of which reach the first and second buried layers. A
PN junction formed between the first and second base layers
and first and second buried layers is then simply a planar
junction.